Datasheet



650V 20A Field Stop Trench IGBT

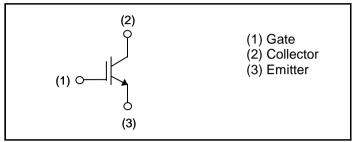
V_{CES}	650V
I _C	20A
V _{CE(sat) (Typ.)}	1.65V
P_D	177W

Outline LPDL (TO-263L)

Features

- 1) Qualified to AEC-Q101
- 2) Low Collector Emitter Saturation Voltage
- 3) Short Circuit Withstand Time 8µs
- 4) Pb free Lead Plating; RoHS Compliant

●Inner Circuit



Application

General Inverter

for Automotive and Industrial Use

Heater for Automotive

Packaging Specifications

Prackaging Specifications					
	Packaging	Taping			
	Reel Size (mm)	330			
Typo	Tape Width (mm)	24			
F	Basic Ordering Unit (pcs)	1,000			
	Packing Code	TL			
	Marking	RGS40NL65			

● **Absolute Maximum Ratings** (at T_C = 25°C unless otherwise specified)

	<u> </u>	, ,		
Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	T _C = 25°C	I _C	42	А
Collector Current	T _C = 100°C	I _C	28	Α
Pulsed Collector Current	Ised Collector Current		60	Α
Power Dissipation	T _C = 25°C	P _D	177	W
	T _C = 100°C	P _D	88	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raidilletei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	ı	0.85	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

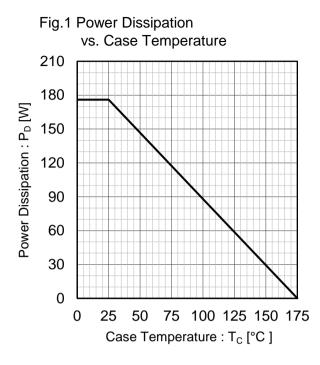
Parameter	Symbol	Conditions		Unit		
- raiailletei	Gonditions Conditions		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10\mu A, V_{GE} = 0V$	650	-	-	V
		$V_{CE} = 650V, V_{GE} = 0V,$				_
Collector Cut - off Current	I _{CES}	T _j = 25°C	-	-	10	μΑ
		Tj = 175°C	-	0.1	-	mA
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 1.0mA$	5.0	6.0	7.0	V
		$I_C = 20A, V_{GE} = 15V,$				
Collector - Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	T _j = 25°C	-	1.65	2.10	V
		T _j = 175°C	-	2.15	-	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Danamatan	Curanha al	Conditions		l lmit		
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	$V_{CE} = 30V$,	-	881	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$,	-	55	-	рF
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	7	-	
Total Gate Charge	Q_g	V _{CE} = 400V,	-	28	-	
Gate - Emitter Charge	Q_ge	$I_{\rm C} = 20A$,	-	7	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	11	-	
Turn - on Delay Time	t _{d(on)}		-	24	-	
Rise Time	t _r	$I_C = 20A, V_{CC} = 400V,$ $V_{GF} = 15V, R_G = 10\Omega,$	-	12	-	
Turn - off Delay Time	t _{d(off)}	$T_i = 25^{\circ}C$	-	87	-	ns
Fall Time	t _f	Inductive Load	-	89	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	0.56	-	mJ
Turn - off Switching Loss	E _{off}	,	-	0.49	-	
Turn - on Delay Time	t _{d(on)}		-	24	-	
Rise Time	t _r	$I_C = 20A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	15	-	ns
Turn - off Delay Time	t _{d(off)}	$T_i = 175^{\circ}C$	-	104	-	
Fall Time	t _f	Inductive Load	-	114	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	0.60	-	mJ
Turn - off Switching Loss	E _{off}	1000100 10000019	-	0.65	-	1113
		$I_C = 60A, V_{CC} = 520V,$				-
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V,$	FULL SQUARE			
		$R_G = 50\Omega, T_j = 175^{\circ}C$				
Short Circuit Withstand Time	t _{sc}	$V_{CC} \le 360V$, $V_{GE} = 15V$, $T_j = 25^{\circ}C$	8	-	-	μs
Short Circuit Withstand Time	t _{sc} *2	$V_{CC} \le 360V$, $V_{GE} = 15V$, $T_j = 150$ °C	6	-	-	μs

^{*2} Design assurance without measurement

•Electrical Characteristic Curves



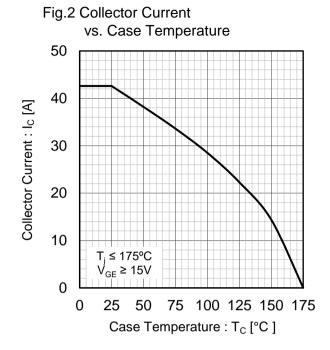


Fig.3 Forward Bias Safe Operating Area

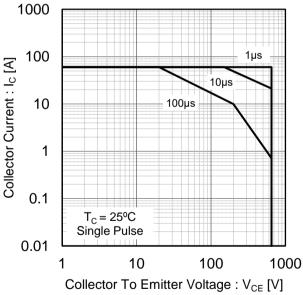
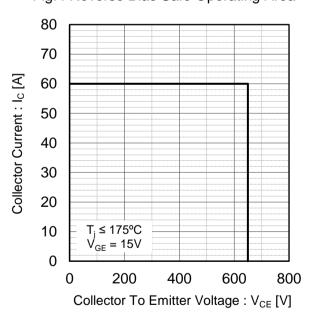


Fig.4 Reverse Bias Safe Operating Area



• Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

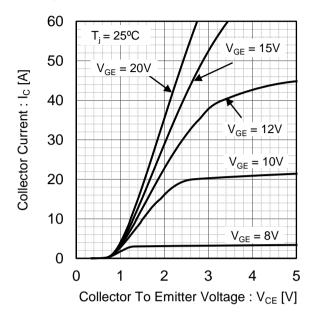


Fig.6 Typical Output Characteristics

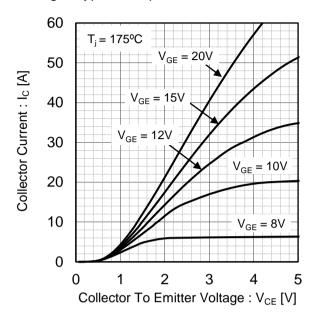


Fig.7 Typical Transfer Characteristics

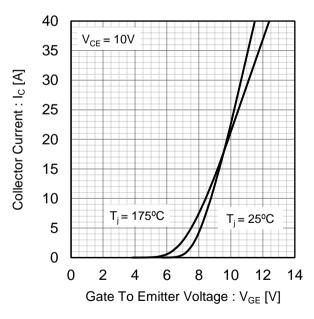
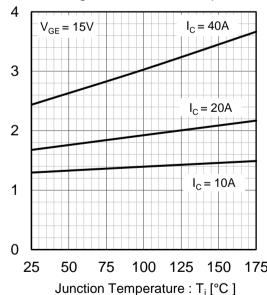


Fig.8 Typical Collector To Emitter Saturation
Voltage vs. Junction Temperature



Collector To Emitter Saturation Voltage

: V_{CE(sat)} [V]

•Electrical Characteristic Curves

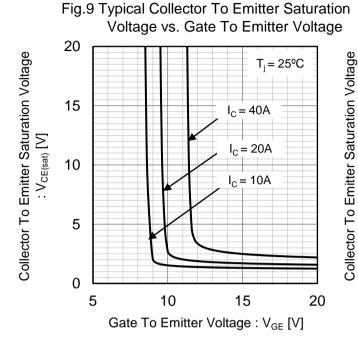


Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

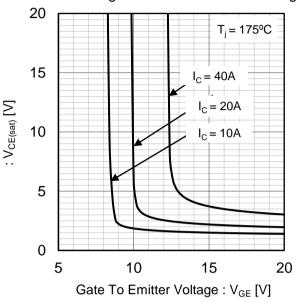
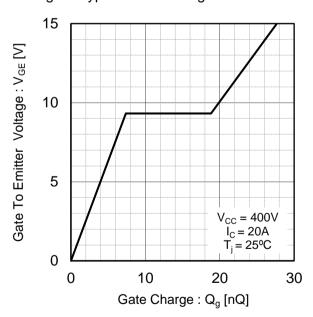
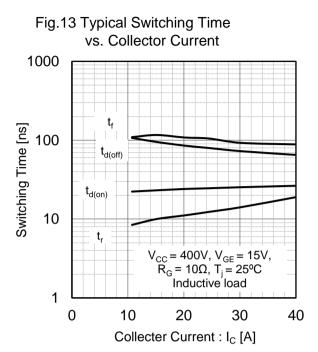


Fig.11 Typical Capacitance vs. Collector To Emitter Voltage 10000 Capacitance [pF] 1, \mathbf{C}_{ies} C_{oes} 10 f = 1MHz $V_{GE} = 0V$ $T_i = 25^{\circ}C$ C_{res} 1 0.01 0.1 10 100 Collector To Emitter Voltage: V_{CE} [V]

Fig.12 Typical Gate Charge



• Electrical Characteristic Curves



vs. Gate Resistance 1000 Switching Time [ns] 100 $t_{\text{d(off)}}$ $\mathsf{t}_{\mathsf{d}(\mathsf{on})}$ 10 $V_{CC} = 400V, V_{GE} = 15V,$ $I_{C} = 20A, T_{j} = 25^{\circ}C$ Inductive load 1 0 10 20 30 50 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Time

Fig.15 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ 0.1 E_{on} V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10 Ω , T_{j} = 25°C Inductive load 0.01 0 10 20 30 40 Collector Current : I_C [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ E_{on} 0.1 V_{CC} = 400V, V_{GE} = 15V, I_{C} = 20A, T_{j} = 25°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.16 Typical Switching Energy Losses

• Electrical Characteristic Curves

Fig.17 Typical Switching Time vs. Collector Current 1000 t_f Switching Time [ns] 100 $t_{\text{d(off)}}$ $t_{d(on)}$ 10 t_r $V_{CC} = 400V, V_{GE} = 15V,$ $R_G = 10\Omega, T_j = 175^{\circ}C$ Inductive load 1 0 10 20 30 40 Collecter Current : I_C [A]

vs. Gate Resistance 1000 Switching Time [ns] 100 $t_{d(off)}$ $t_{d(on)}$ 10 $V_{CC} = 400V, V_{GE} = 15V,$ $I_{C} = 20A, T_{j} = 175^{\circ}C$ Inductive load 1 0 10 20 30 50 Gate Resistance : $R_G[\Omega]$

Fig.18 Typical Switching Time

Fig.19 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ 0.1 E_{on} V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10 Ω , T_{j} = 175°C Inductive load 0.01 0 10 20 30 40 Collector Current : I_C [A]

vs. Gate Resistance

10

See Section 1

Eoff $V_{CC} = 400V, V_{GE} = 15V, I_{C} = 20A, T_{j} = 175^{\circ}C$ Inductive load

0.01

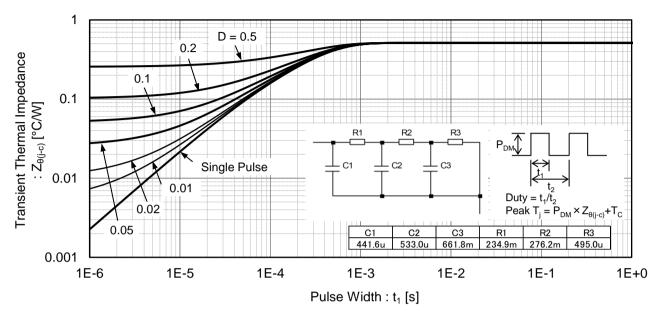
0 10 20 30 40 50

Gate Resistance : R_{G} [Ω]

Fig.20 Typical Switching Energy Losses

•Electrical Characteristic Curves

Fig.21 Typical IGBT Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

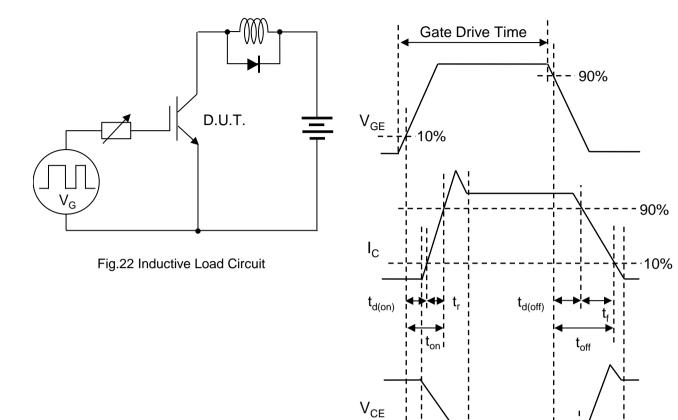


Fig.23 Inductive Load Waveform

E_{on}

·10%

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